ABSTRACT OF THE DISCLOSURE

A thin-film semiconductor device is provided including a plurality of thin-film transistors (TFT) having different driving voltages formed on an glass substrate, wherein a gate electrode electric field at each of the driving voltages of the plurality of thin-film transistors is in a range of about 1MV/cm to 2MV/cm, and a drain concentration of p-type thin-film transistors (TFT) is in a range of about $3E+19/cm^3$ to $1E+20/cm^3$.